

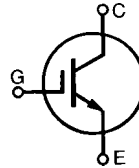
IGBT

High Voltage, Low $V_{CE(sat)}$

IXGH 45N120
IXGT 45N120

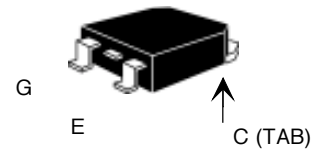
$V_{CES} = 1200 \text{ V}$
 $I_{C25} = 75 \text{ A}$
 $V_{CE(sat)} = 2.5 \text{ V}$
 $t_{fi(typ)} = 390 \text{ ns}$

Preliminary data sheet

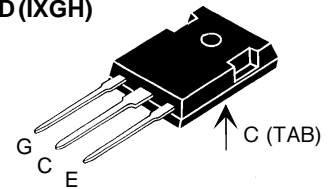


Symbol	Test Conditions	Maximum Ratings
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200 V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	1200 V
V_{GES}	Continuous	$\pm 20 \text{ V}$
V_{GEM}	Transient	$\pm 30 \text{ V}$
I_{C25}	$T_C = 25^\circ\text{C}$, limited by leads	75 A
I_{C90}	$T_C = 90^\circ\text{C}$	45 A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	180 A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 5 \Omega$ Clamped inductive load	$I_{CM} = 90 \text{ A}$ @ $0.8 V_{CES}$
P_C	$T_C = 25^\circ\text{C}$	300 W
T_J		-55 ... +150 $^\circ\text{C}$
T_{JM}		150 $^\circ\text{C}$
T_{stg}		-55 ... +150 $^\circ\text{C}$
Maximum Lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300 $^\circ\text{C}$
Maximum Tab temperature for soldering SMD devices for 10 s		260 $^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10Nm/lb.in.
Weight	TO-247 AD	6 g
	TO-268	4 g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages JEDEC TO-268 and JEDEC TO-247 AD
- High current handling capability
- MOS Gate turn-on - drive simplicity
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- Capacitor discharge

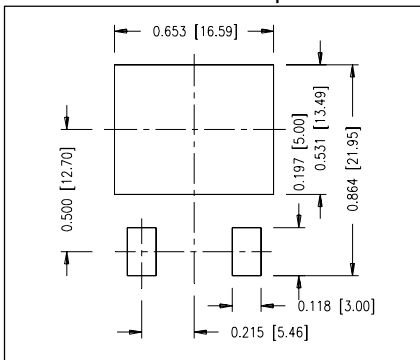
Advantages

- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

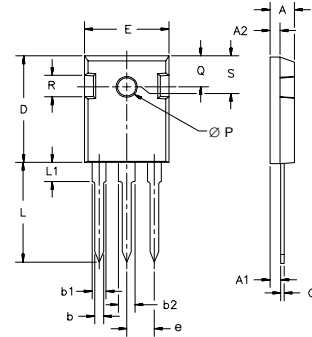
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 1 \text{ mA}$, $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 750 \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		250 μA
		$T_J = 125^\circ\text{C}$		2 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$			2.5 V

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	33	44	S
$I_{C(ON)}$	$V_{GE} = 10\text{ V}, V_{CE} = 10\text{ V}$		220	A
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		4700	pF
C_{oes}		255	pF	
C_{res}		89	pF	
Q_g	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		170	nC
Q_{ge}		28	nC	
Q_{gc}		57	nC	
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$		55	ns
t_{ri}	$I_C = I_{C90}, V_{GE} = 15\text{ V}$		28	ns
$t_{d(off)}$	$V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 5\ \Omega$		370	800 ns
t_{fi}	Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$,		390	700 ns
E_{off}	higher T_J or increased R_G		14	25 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$		64	ns
t_{ri}	$I_C = I_{C90}, V_{GE} = 15\text{ V}$		32	ns
E_{on}	$V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 5\ \Omega$		3.0	mJ
$t_{d(off)}$	Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$,		660	ns
t_{fi}	higher T_J or increased R_G		740	ns
E_{off}			25	mJ
R_{thJC}				0.42 KW
R_{thCK}	(TO-247)		0.25	KW

Min Recommended Footprint

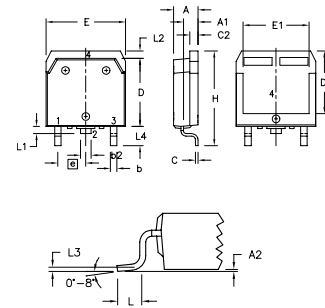


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-268 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025